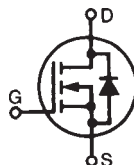


# TrenchT2™ Power MOSFET

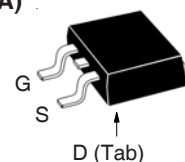
## IXTA100N04T2 IXTP100N04T2

N-Channel Enhancement Mode  
Avalanche Rated

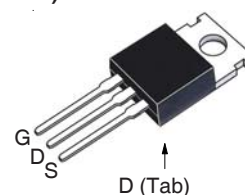


$$\begin{aligned} V_{DSS} &= 40V \\ I_{D25} &= 100A \\ R_{DS(on)} &\leq 7m\Omega \end{aligned}$$

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate      D = Drain  
S = Source    Tab = Drain

| Symbol     | Test Conditions                                                   | Maximum Ratings    |                  |
|------------|-------------------------------------------------------------------|--------------------|------------------|
| $V_{DSS}$  | $T_J = 25^\circ\text{C to } 175^\circ\text{C}$                    | 40                 | V                |
| $V_{DGR}$  | $T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GS} = 1M\Omega$ | 40                 | V                |
| $V_{GSM}$  | Transient                                                         | $\pm 20$           | V                |
| $I_{D25}$  | $T_C = 25^\circ\text{C}$                                          | 100                | A                |
| $I_{DM}$   | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$        | 300                | A                |
| $I_A$      | $T_C = 25^\circ\text{C}$                                          | 50                 | A                |
| $E_{AS}$   | $T_C = 25^\circ\text{C}$                                          | 300                | mJ               |
| $P_D$      | $T_C = 25^\circ\text{C}$                                          | 150                | W                |
| $T_J$      |                                                                   | -55 ... +175       | $^\circ\text{C}$ |
| $T_{JM}$   |                                                                   | 175                | $^\circ\text{C}$ |
| $T_{stg}$  |                                                                   | -55 ... +175       | $^\circ\text{C}$ |
| $T_L$      | Maximum Lead Temperature for Soldering                            | 300                | $^\circ\text{C}$ |
| $T_{SOLD}$ | 1.6 mm (0.062in.) from Case for 10s                               | 260                | $^\circ\text{C}$ |
| $F_C$      | Mounting Force (TO-263)                                           | 10..65 / 2.2..14.6 | N/lb             |
| $M_d$      | Mounting Torque (TO-220)                                          | 1.13 / 10          | Nm/lb.in         |
| Weight     | TO-263                                                            | 2.5                | g                |
|            | TO-220                                                            | 3.0                | g                |

### Features

- International Standard Packages
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- 175°C Operating Temperature
- High Current Handling Capability
- ROHS Compliant
- High Performance Trench Technology for extremely low  $R_{DS(on)}$

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Automotive Engine Control
- Synchronous Buck Converter (for Notebook SystemPower & General Purpose Point & Load)
- DC/DC Converters
- High Current Switching Applications
- Power Train Management
- Distributed Power Architecture

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values |      |              |
|--------------|---------------------------------------------------------------------------|-----------------------|------|--------------|
|              |                                                                           | Min.                  | Typ. | Max.         |
| $BV_{DSS}$   | $V_{GS} = 0V, I_D = 250\mu A$                                             | 40                    |      | V            |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$                                         | 2.0                   |      | 4.0 V        |
| $I_{GSS}$    | $V_{GS} = \pm 20V, V_{DS} = 0V$                                           |                       |      | $\pm 100$ nA |
| $I_{DSS}$    | $V_{DS} = V_{DSS}, V_{GS} = 0V$                                           |                       |      | 2 $\mu A$    |
|              | $T_J = 150^\circ\text{C}$                                                 |                       |      | 50 $\mu A$   |
| $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 25A$ , Notes 1 & 2                                   |                       |      | 7 m $\Omega$ |

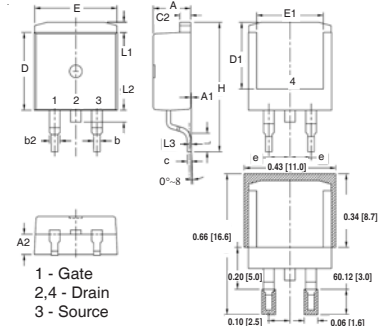
| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                                                            | Characteristic Values |      |                        |
|--------------|--------------------------------------------------------------------------------------------------------------------------------------|-----------------------|------|------------------------|
|              |                                                                                                                                      | Min.                  | Typ. | Max.                   |
| $g_{fs}$     | $V_{DS} = 10\text{V}$ , $I_D = 50\text{A}$ , Note 1                                                                                  | 27                    | 45   | S                      |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                     |                       | 2690 | pF                     |
| $C_{oss}$    |                                                                                                                                      |                       | 490  | pF                     |
| $C_{rss}$    |                                                                                                                                      |                       | 105  | pF                     |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 20\text{V}$ , $I_D = 50\text{A}$<br>$R_G = 5\Omega$ (External) |                       | 12.0 | ns                     |
| $t_r$        |                                                                                                                                      |                       | 5.2  | ns                     |
| $t_{d(off)}$ |                                                                                                                                      |                       | 15.8 | ns                     |
| $t_f$        |                                                                                                                                      |                       | 6.4  | ns                     |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{DSS}$                                                     |                       | 25.5 | nC                     |
| $Q_{gs}$     |                                                                                                                                      |                       | 8.0  | nC                     |
| $Q_{gd}$     |                                                                                                                                      |                       | 5.7  | nC                     |
| $R_{thJC}$   | TO-220                                                                                                                               |                       | 0.50 | $1.00^\circ\text{C/W}$ |
| $R_{thCS}$   |                                                                                                                                      |                       |      | $^\circ\text{C/W}$     |

#### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                              | Characteristic Values |      |       |
|----------|--------------------------------------------------------------------------------------------------------|-----------------------|------|-------|
|          |                                                                                                        | Min.                  | Typ. | Max.  |
| $I_S$    | $V_{GS} = 0\text{V}$                                                                                   |                       |      | 100 A |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$                                                            |                       |      | 400 A |
| $V_{SD}$ | $I_F = 50\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1                                                     |                       |      | 1.2 V |
| $t_{rr}$ | $I_F = 50\text{A}$ , $V_{GS} = 0\text{V}$ ,<br>$-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 20\text{V}$ |                       | 34   | ns    |
| $I_{RM}$ |                                                                                                        |                       | 1.44 | A     |
| $Q_{RM}$ |                                                                                                        |                       | 24.5 | nC    |

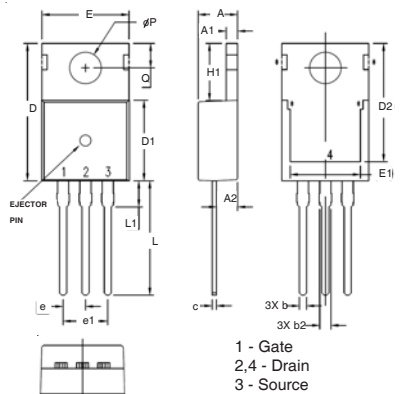
- Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .  
2. On through-hole packages,  $R_{DS(on)}$  Kelvin test contact location must be 5mm or less from the package body.

#### TO-263 Outline



| SYM  | INCHES   |      | MILLIMETER |       |
|------|----------|------|------------|-------|
|      | MIN      | MAX  | MIN        | MAX   |
| A    | .170     | .185 | 4.30       | 4.70  |
| A1   | .000     | .008 | 0.00       | 0.20  |
| A2   | .091     | .098 | 2.30       | 2.50  |
| b    | .028     | .035 | 0.70       | 0.90  |
| b2   | .046     | .060 | 1.18       | 1.52  |
| C    | .018     | .024 | 0.45       | 0.60  |
| C2   | .049     | .060 | 1.25       | 1.52  |
| D    | .340     | .370 | 8.63       | 9.40  |
| D1   | .300     | .327 | 7.62       | 8.30  |
| E    | .380     | .410 | 9.65       | 10.41 |
| E1   | .270     | .330 | 6.86       | 8.38  |
| [e]  | .100 BSC |      | 2.54 BSC   |       |
| H    | .580     | .620 | 14.73      | 15.75 |
| L    | .075     | .105 | 1.91       | 2.67  |
| L1   | .039     | .060 | 1.00       | 1.52  |
| L2   | —        | .070 | —          | 1.77  |
| [L3] | .010 BSC |      | 0.254 BSC  |       |

#### TO-220 Outline



| SYM  | INCHES   |      | MILLIMETERS |       |
|------|----------|------|-------------|-------|
|      | MIN      | MAX  | MIN         | MAX   |
| A    | .169     | .185 | 4.30        | 4.70  |
| A1   | .047     | .055 | 1.20        | 1.40  |
| A2   | .079     | .106 | 2.00        | 2.70  |
| b    | .024     | .039 | 0.60        | 1.00  |
| b2   | .045     | .057 | 1.15        | 1.45  |
| c    | .014     | .026 | 0.35        | 0.65  |
| D    | .587     | .626 | 14.90       | 15.90 |
| D1   | .335     | .370 | 8.50        | 9.40  |
| (D2) | .500     | .531 | 12.70       | 13.50 |
| E    | .382     | .406 | 9.70        | 10.30 |
| (E1) | .283     | .323 | 7.20        | 8.20  |
| e    | .100 BSC |      | 2.54 BSC    |       |
| e1   | .200 BSC |      | 5.08 BSC    |       |
| H1   | .244     | .268 | 6.20        | 6.80  |
| L    | .492     | .547 | 12.50       | 13.90 |
| L1   | .110     | .154 | 2.80        | 3.90  |
| ØP   | .134     | .150 | 3.40        | 3.80  |
| Q    | .106     | .126 | 2.70        | 3.20  |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

|                                                                                  |           |           |           |           |             |             |             |             |             |             |
|----------------------------------------------------------------------------------|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665   | 6,404,065B1 | 6,683,344   | 6,727,585   | 7,005,734B2 | 7,157,338B2 |
|                                                                                  | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343   | 6,710,405B2 | 6,759,692   | 7,063,975B2 |             |
|                                                                                  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505   | 6,710,463   | 6,771,478B2 | 7,071,537   |             |

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**

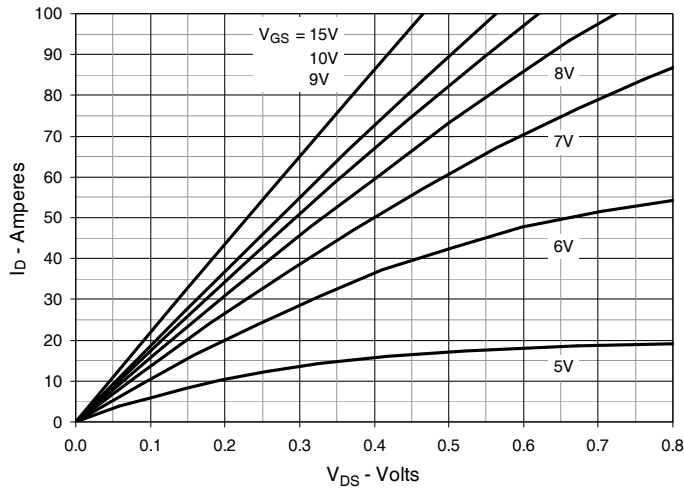


**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**

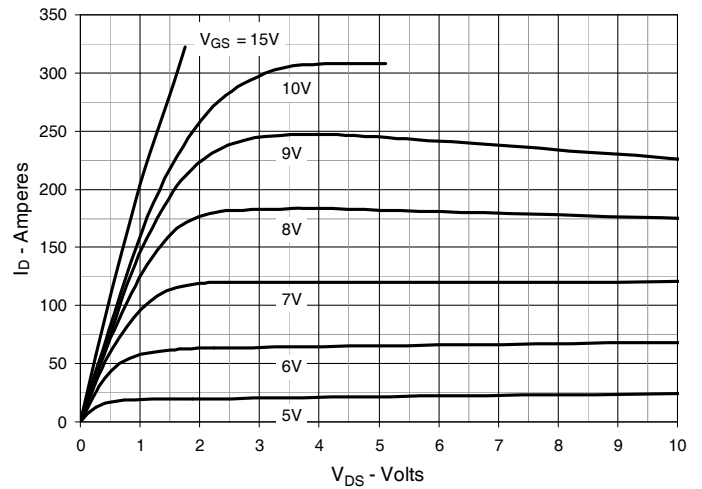


**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**

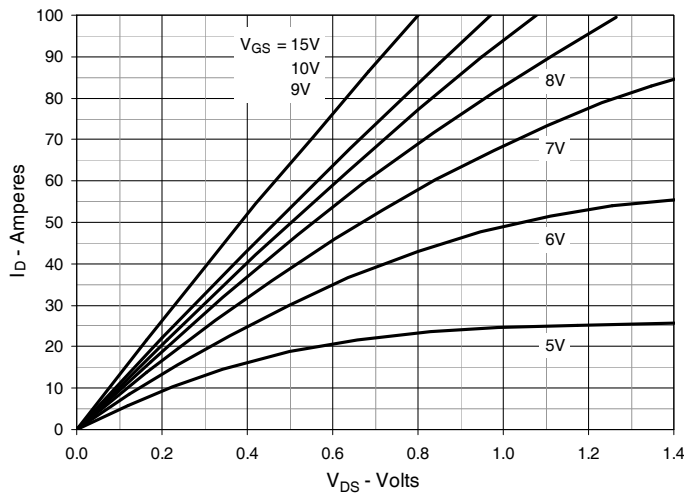


**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 50\text{A}$  Value vs. Junction Temperature**

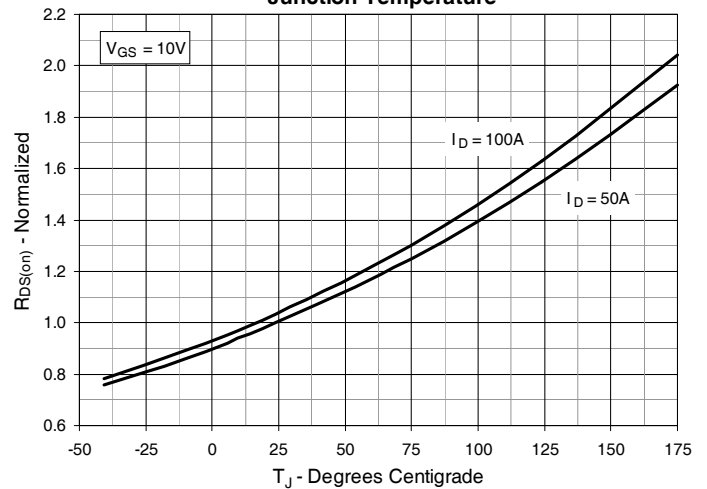


**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 50\text{A}$  Value vs. Drain Current**

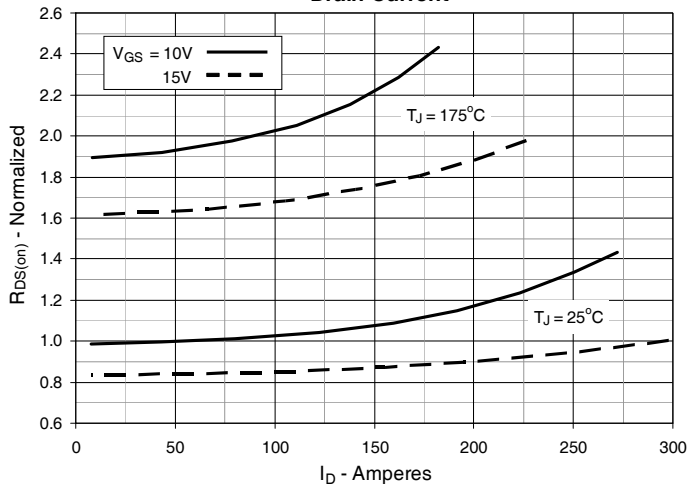


**Fig. 6. Drain Current vs. Case Temperature**

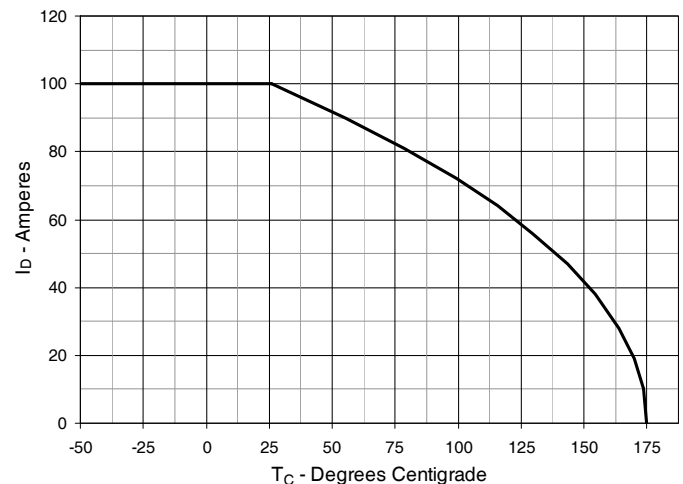


**Fig. 7. Input Admittance**

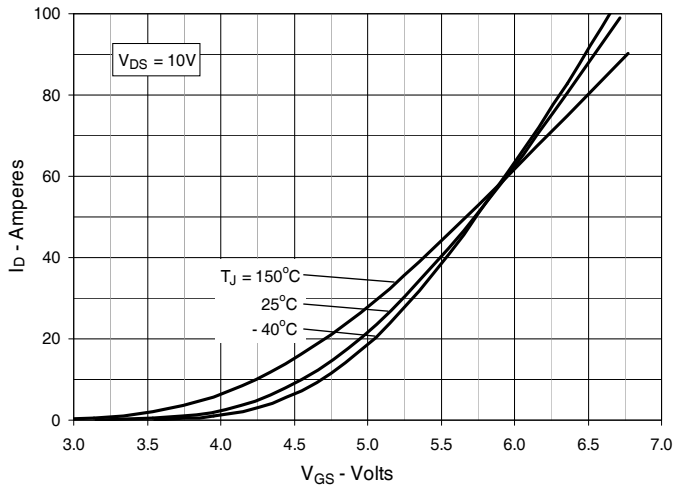


**Fig. 8. Transconductance**

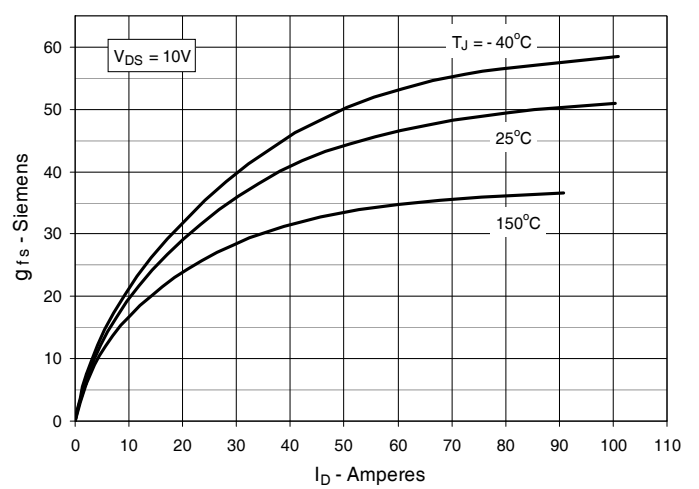


**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

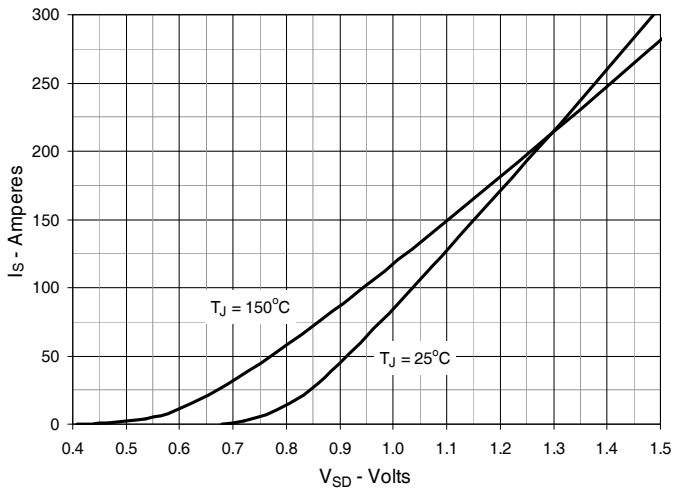


**Fig. 10. Gate Charge**

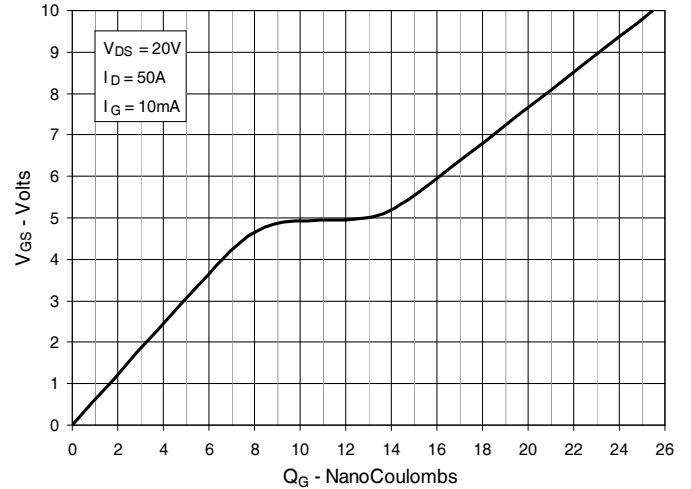


**Fig. 11. Capacitance**

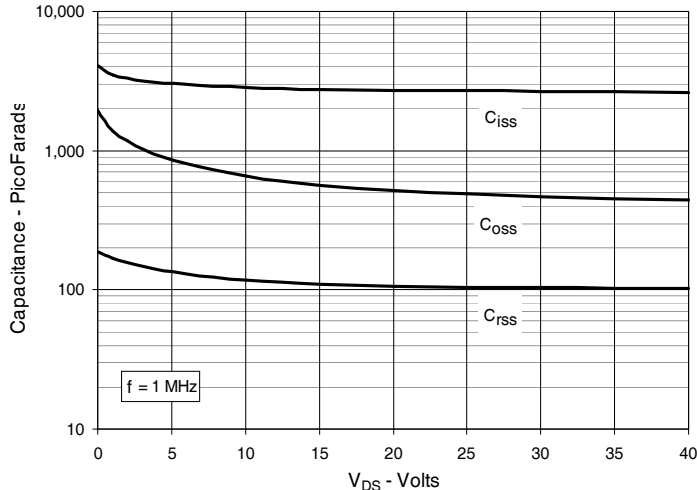


**Fig. 12. Forward-Bias Safe Operating Area**

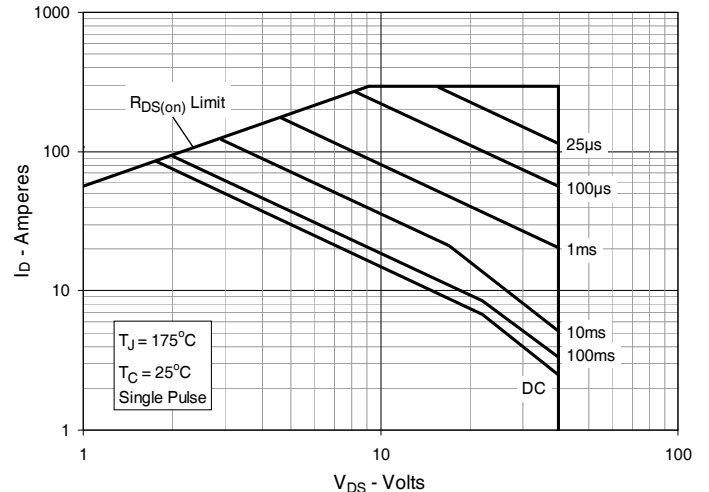


**Fig. 13. Resistive Turn-on**  
**Rise Time vs. Junction Temperature**

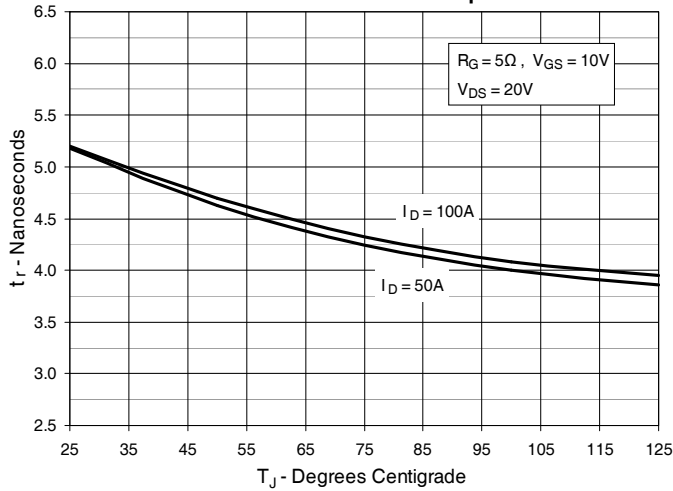


**Fig. 14. Resistive Turn-on**  
**Rise Time vs. Drain Current**

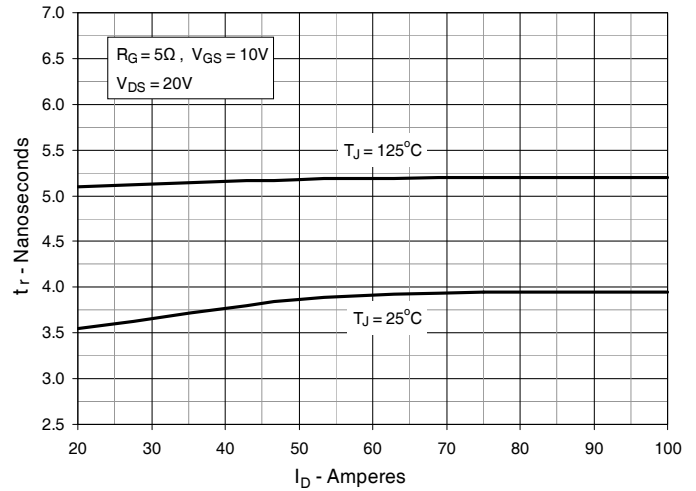


**Fig. 15. Resistive Turn-on**  
**Switching Times vs. Gate Resistance**

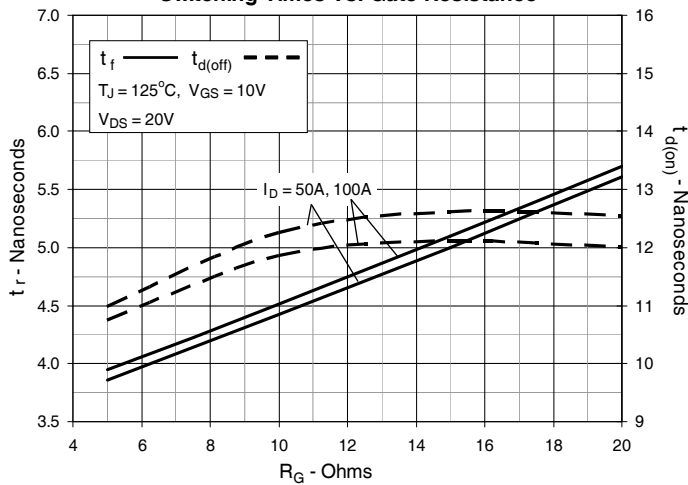


**Fig. 16. Resistive Turn-off**  
**Switching Times vs. Junction Temperature**

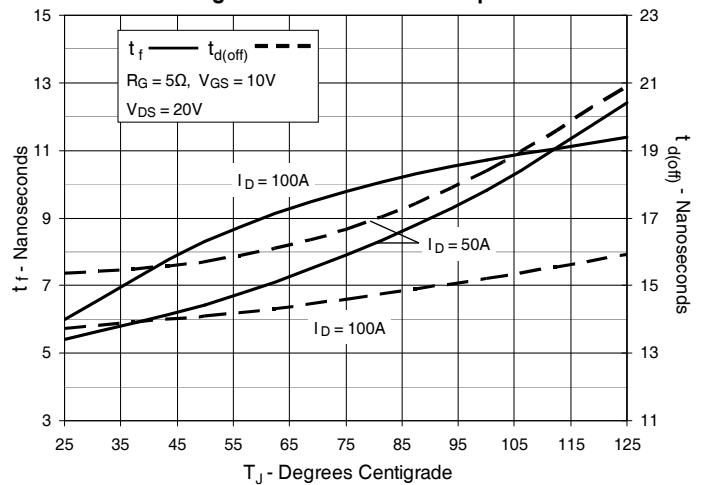


**Fig. 17. Resistive Turn-off**  
**Switching Times vs. Drain Current**

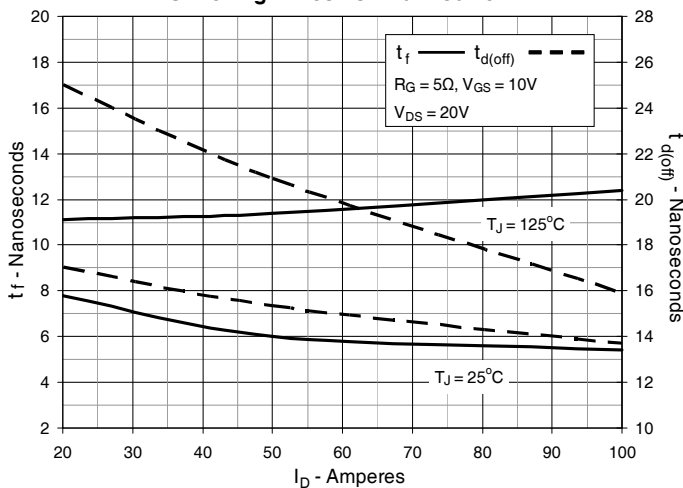


**Fig. 18. Resistive Turn-off**  
**Switching Times vs. Gate Resistance**

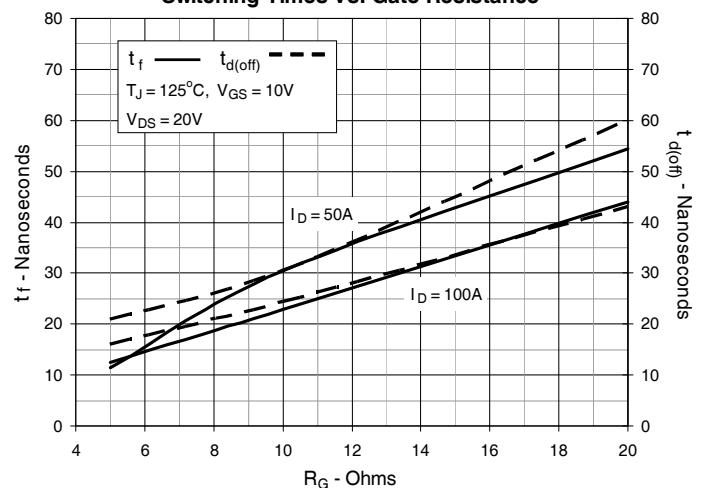
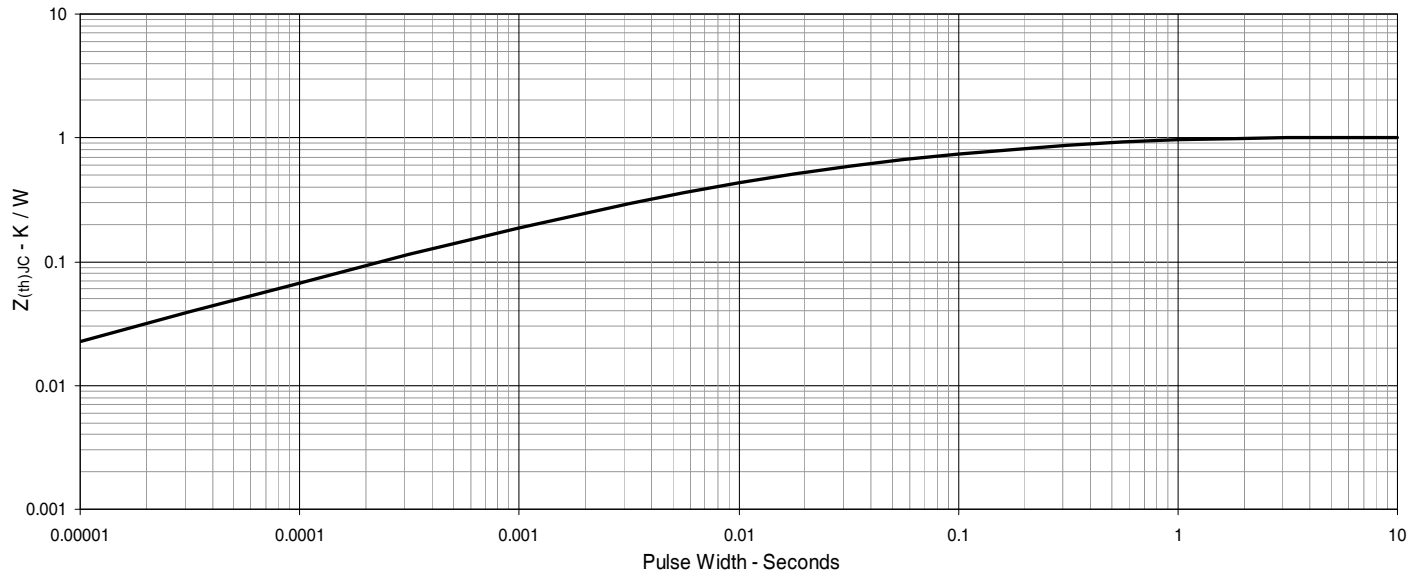


Fig. 19. Maximum Transient Thermal Impedance





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